# Supporting Information for

# Tuning of Electronic Transport Characteristics of ZnO Micro/Nanowire Piezotronic Schottky Diodes by Bending: Threshold Voltage Shift

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**Figure S1** The *I-V* characteristics of the fabricated devices under the dark and the UV light illumination. The loading forces on the straight and bent ZnO wires are 5 nN and 160 nN. The inset shows the schematic diagram of the UV light illumination on the ZnO wire.

**Figure S2** Fitting the plots of ln *I* vs *V* of the bent ZnO wire under the dark and the UV light illumination. The solid curves are accomplished by fitting the experimental data points.

**Figure S3** The *I-V* curves of the fabricated device based on a single ZnO wire with the diameter of 1.8 μm under the loading forces of 5 nN and 160 nN. The inset is a SEM of the single ZnO wire.

**Figure S4** The *I-V* curves of the fabricated device based on a single ZnO wire with the diameter of 2.3 μm under the loading forces of 5 nN and 160 nN. The inset is a SEM of the single ZnO wire.

**Figure S5** The *I-V* curves of the fabricated device based on a single ZnO wire with the diameter of 2.7 μm under the loading forces of 5 nN and 160 nN. The inset is a SEM of the single ZnO wire.

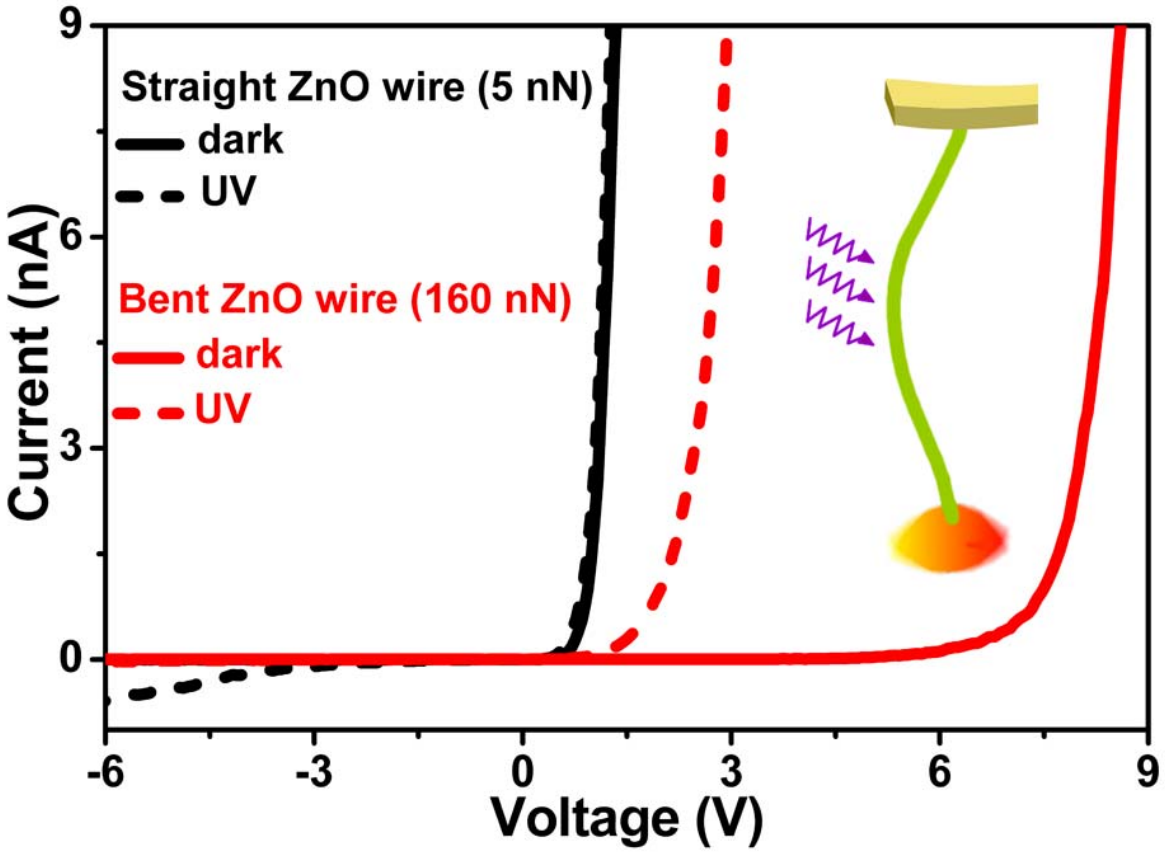


**Figure S1**

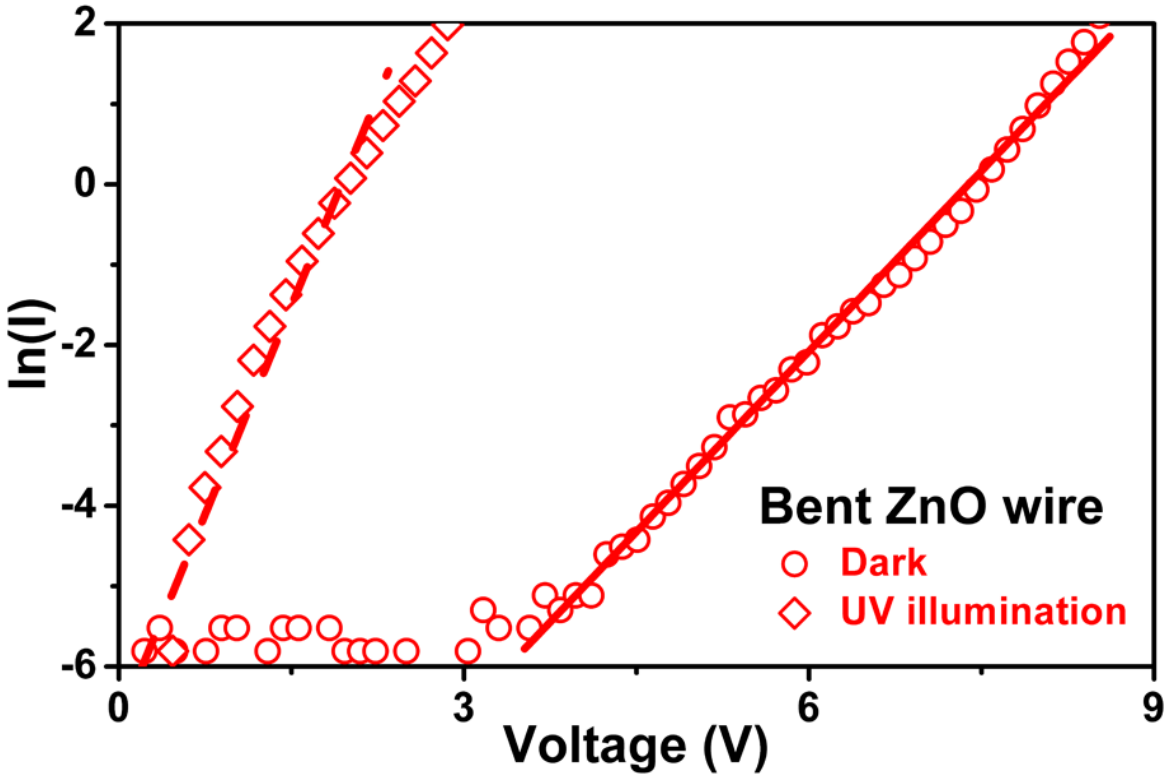


**Figure S2**

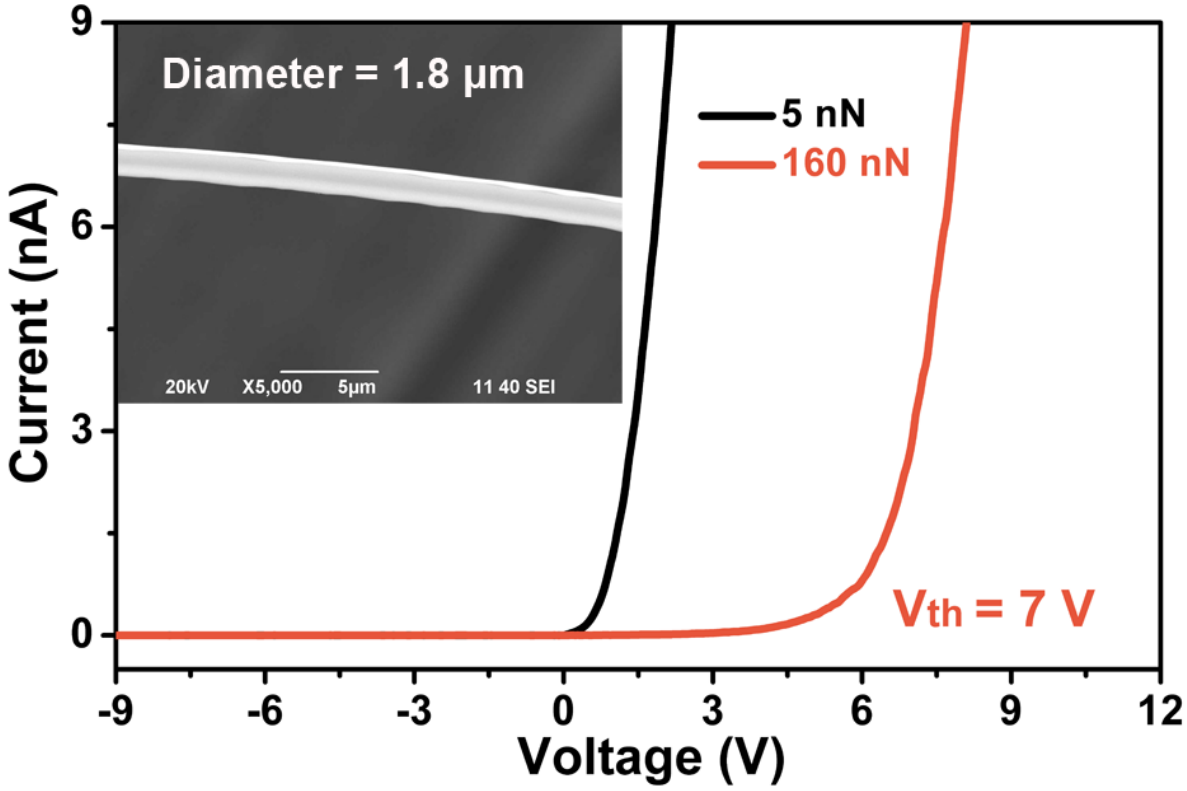


**Figure S3**

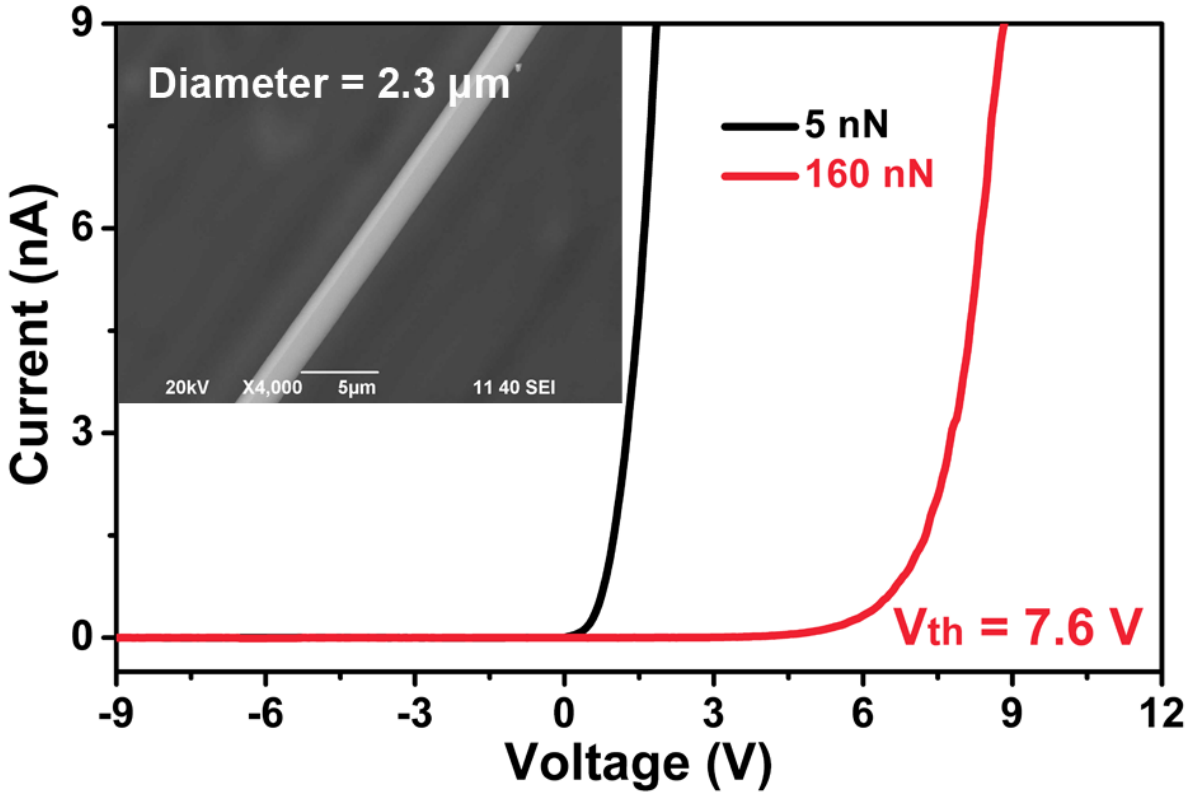


**Figure S4**

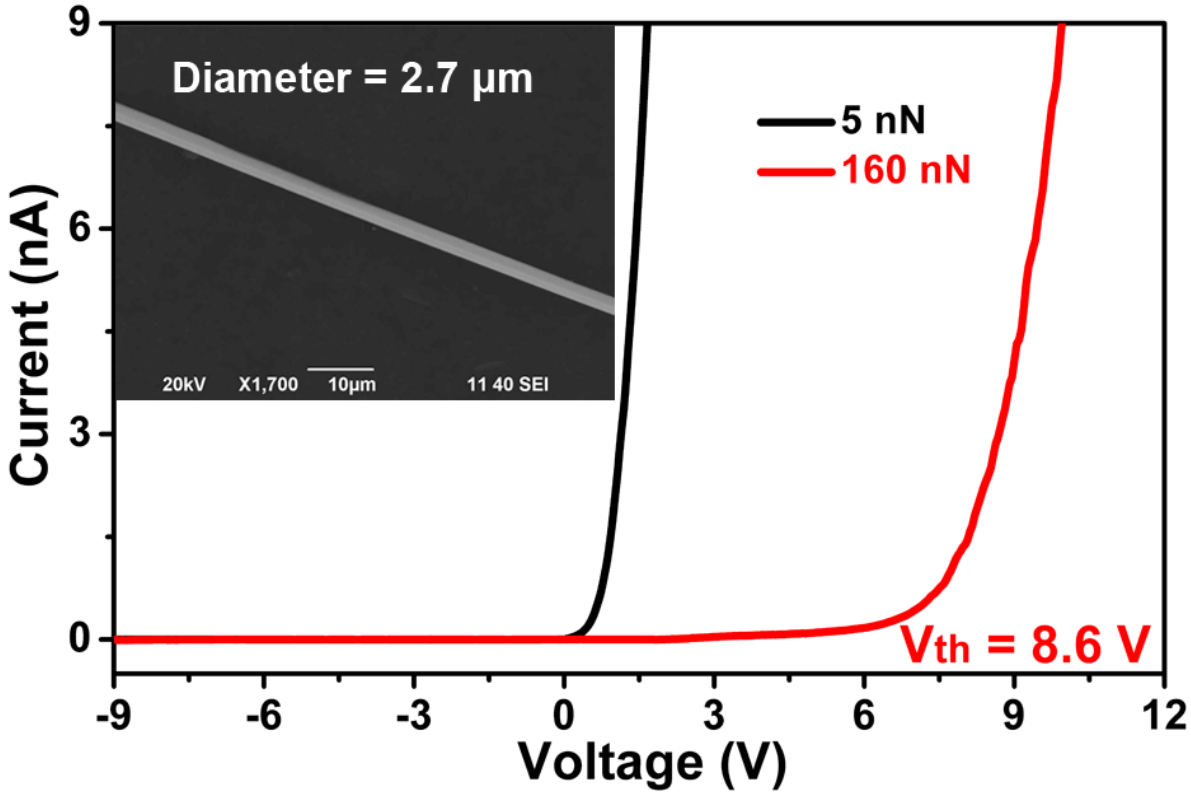


**Figure S5**